## SILICON SCHOTTKY BARRIER DIODE

## Features

- Low reverse current, low capacitance
- Ultra small flat package is suitable for surface mount design

PINNING

| PIN | DESCRIPTION |
| :---: | :--- |
| 1 | Cathode |
| 2 | Anode |



Top View
Marking Code: "W"
Simplified outline SOD-523 and symbol

Absolute Maximum Ratings ( $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$ )

| Parameter | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Repetitive Peak Reverse Voltage | $\mathrm{V}_{\text {RRM }}$ | 25 | V |
| Forward Current | $\mathrm{I}_{\mathrm{F}}$ | 50 | mA |
| Non-Repetitive Peak Forward Surge Current | $\mathrm{I}_{\mathrm{FSM}}$ | 200 | mA |
| Junction Temperature Range | $\mathrm{T}_{\mathrm{j}}$ | 125 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $\mathrm{T}_{\mathrm{s}}$ | -55 to +125 | ${ }^{\circ} \mathrm{C}$ |

Characteristics at $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$

| Parameter | Symbol | Max. | Unit |
| :--- | :---: | :---: | :---: |
| Forward Voltage <br> at $\mathrm{I}_{\mathrm{F}}=1 \mathrm{~mA}$ <br> at $\mathrm{I}_{\mathrm{F}}=5 \mathrm{~mA}$ | $\mathrm{~V}_{\mathrm{F}}$ | 0.33 | V |
| Reverse Current <br> at $\mathrm{V}_{\mathrm{R}}=20 \mathrm{~V}$ | $\mathrm{I}_{\mathrm{R}}$ | 0.38 | $\mathrm{\mu A}$ |
| Capacitance <br> at $\mathrm{V}_{\mathrm{R}}=1 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ | C | 2.85 | pF |



Fig. 1 Forwand current vs. Fonward voltage


Fig. 3 Capacitance Vs. Reverse voltage


Fig. 2 Reverse current Vs. Reverse voltage

## PACKAGE OUTLINE



| UNIT | A | $\mathrm{b}_{\mathrm{p}}$ | C | D | E | $\mathrm{H}_{\mathrm{E}}$ | V | $\angle$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| mm | 0.70 | 0.4 | 0.135 | 1.25 | 0.85 | 1.7 | 0.1 | $5^{\circ}$ |
|  | 0.60 | 0.3 | 0.127 | 1.15 | 0.75 | 1.5 |  |  |

